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Accurate Measurement of Dynamic ON-state Resistances of GaN Devices under Reverse and Forward Conduction in High Frequency Power Converter

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***Abstract*—Because of trapped charges in GaN transistor structure, device dynamic ON-state resistance R_{DSon} is increased when it is operated in high frequency switched power converters, in which device is possibly operated by zero voltage switching (ZVS) to reduce its turn-ON switching losses. When GaN transistor finishes ZVS during one switching period, device has been operated under both reverse and forward conduction. Therefore its dynamic R_{DSon} under both conduction modes needs to be carefully measured to understand device power losses. For this reason, a measurement circuit with simple structure and fast dynamic response is proposed to characterise device reverse and forward R_{DSon}. In order to improve measurement sensitivity when device switches at high frequency, a trapezoidal current mode is proposed to measure device R_{DSon} under almost constant current, which resolves measurement sensitivity issues caused by unavoidable measurement circuit parasitic inductance and measurement probes deskew in conventional device characterisation method by triangle current mode. Proposed measurement circuit and measurement method is then validated by first characterising a SiC-MOSFET with constant R_{DSon}. Then, the comparison on GaN-HEMT dynamic R_{DSon} measurement results demonstrates the improved accuracy of proposed trapezoidal current mode over conventional triangle current mode when device switches at 1MHz.**

***Index Terms*—GaN transistor, dynamic ON-state resistance, high switching frequency, reverse conduction, forward conduction, soft switching**

I. INTRODUCTION

Because of low power losses and fast switching transition, integrating gallium nitride (GaN) power semiconductor devices into high frequency electrical energy conversion systems is becoming a hot research topic [1]–[4] to increase power converter power density. To design high frequency power converters, device power losses estimation becomes very important, as it determines whole system cooling equipment size, which is a key factor to influence on system power density. However, unlike silicon (Si) or silicon carbide (SiC) devices, GaN device has an unwanted characteristic, which is caused by the trapped charge in device buffer layer when device is in OFF-state. Those trapped charges will reduce device current conduction capability, resulting in increased ON-state resistance (R_{DSon}) compared with device theoretical value. It is to be noted that GaN device dynamic R_{DSon} values are normally not given in device datasheet, which makes its conduction power losses unpredictable in application. Furthermore, power semiconductor devices R_{DSon} is an important parameter for power electronics systems diagnosis, which can be used as an indicator to study the degradation of both device [5] and packaging [6]. Therefore, a clear understanding of GaN device dynamic R_{DSon} is also important for the study of power electronics systems health management. For those reasons, it is necessary to propose new characterisation method to accurately measure GaN device dynamic R_{DSon} in high frequency power converters.

Even though GaN device fabrication process has been improved by different techniques such as field-plate structure [7] and ameliorated device buffer layer [8], [9] to decrease dynamic R_{DSon} value, it is still found in reported research work [10]–[17] that commercial device dynamic R_{DSon} can increase to maximal 5-10 times bigger than device static R_{DSon} value depending on device operation conditions.

GaN device dynamic R_{DSon} measurement method reported in the above research work can be summarised into TABLE I, where there are in general indirect and direct measurement method. In indirect measurement method [10], whole system power losses is measured at first, then with knowledge of other losses present in the active and passive components, the device conduction losses can be indirectly obtained. However, the application of this method in device hard switching operation has not been discussed, as device hard switching losses might cause measurement sensitivity issue, which needs to be further investigated.

In direct measurement method, GaN device conduction current and voltage are measured to obtain R_{DSon}. As illustrated in Fig. 1a, measurement circuit is normally constituted by Device Switching Circuit (DSC), Device Under Test (DUT) and Voltage Clamping Circuit (VCC). The main purpose of DSC (including current source I_{C}) is to control DUT OFF-state, ON-state time and switching conditions. The aim of VCC is to alter the voltage across DUT V_{DS} to the measured voltage $V_{\mathrm{DS(m.)}}$ by $V_{\mathrm{DS(m.)}} = V_{\mathrm{DS}} - \Delta V$, where ΔV is the voltage across VCC. ΔV should equal to V_{DS} when DUT is in OFF-state, while ΔV should be almost zero when DUT is in ON-state for measurement accuracy. Therefore, instead of measuring full range V_{DS} voltage, smaller $V_{\mathrm{DS(m.)}}$ voltage is measured to improve the measurement resolution of the oscilloscope (with 8-bit to 12-bit resolution). It can be also noted that parasitic inductance L_{c} from DUT branch is

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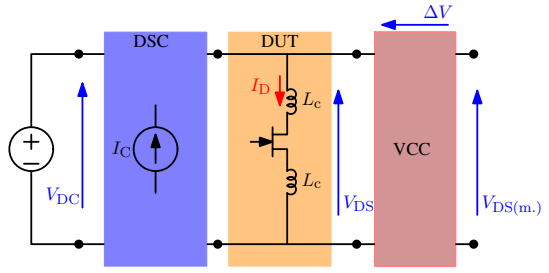
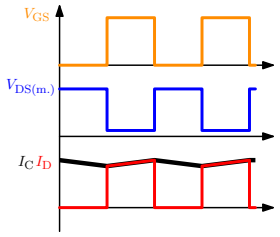
TABLE I: Comparison between the state-of-the-art research work and proposed method in this work to measure GaN device dynamic R_{DSon}

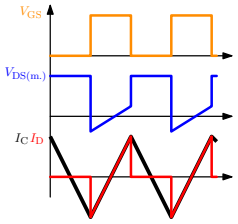
Research work	Method	Switching mode	Current mode & device conduction	Not discussed
Galapon et al. [10]	Indirect	Soft switching	Quasi sinusoidal, forward & reverse	Sensitivity, hard switching
Badawi et al. [11], Cai et al., [12] Yang et al. [13], Foulkes et al., [14] Li et al. [15]	Direct	Hard switching	Quasi constant, forward	Soft switching, reverse current
Lu et al. [16], Li et al. [17]	Direct	Hard & Soft switching	Triangular, forward	Sensitivity, reverse current
This work	Direct	Hard & Soft switching	Trapezoidal, forward & reverse	-



(a) Measurement circuit



(b) DUT hard switching



(c) DUT soft switching via TCM

Fig. 1: Measurement circuit to measure GaN device dynamic R_{DSon} value

appeared in both DSC and VCC part, which is their common L_c when DUT is in operation.

In the published work [11]–[15], authors use different types of the circuit to investigate GaN device dynamic R_{DSon} value under hard switching condition, in which DUT gate source voltage V_{GS}, $V_{\mathrm{DS(m.)}}$ and drain current I_{D} waveform are shown in Fig. 1b (supposing I_{C} is in continuous mode). When DUT is in ON-state, it is always under forward conduction by a quasi constant I_{D}, therefore L_c has little influence on dynamic R_{DSon} measurement results. However, because device can only operate at hard switching in the presented measurement circuits, the above research work cannot be directly applied to investigate GaN device dynamic R_{DSon} value in soft switching condition, where DUT is under reverse conduction.

To extend the method to the case when GaN device is operated in soft switching condition, authors in [16], [17] have proposed a resonant tank in DSC and have controlled DUT in zero voltage switching (ZVS) via triangle current mode (TCM), in which its V_{GS}, $V_{\mathrm{DS(m.)}}$ and I_{D} waveform are shown in Fig. 1c. However, GaN device dynamic R_{DSon} is only measured under forward conduction in the above work. Additionally, measurement sensitivity issue due to voltage drop V_{L_c} by I_{D} fast transition $\mathrm{d}i/\mathrm{d}t$ has not been discussed.

It is important to measure GaN device dynamic R_{DSon} when device is under reverse conduction for the following reasons.

1) Soft switching is an effective method to reduce GaN device switching losses, so device can operate in high frequency (HF) to improve power converter power density. It is necessary to know the dynamic R_{DSon} value immediately after device leaves the OFF-state and begins conduction, but in soft switching operation the device may be in a reverse conduction mode at this time. Only obtaining its dynamic R_{DSon} value under forward conduction may underestimate its conduction losses.
2) During deadtime between two transistors in a phase-leg, current flows reversely through one transistor after turn-OFF of the other. Therefore, it is important to understand this deadtime loss in HF power converters when using GaN devices [18], which requires VCC with reverse current blocking capability and low ΔV under DUT reverse conduction.

Therefore, the main objective of the paper is to accurately measure GaN device dynamic R_{DSon} under both reverse and forward conduction when device operates at HF converter. The main contributions are: 1) To propose a new VCC accordingly. 2) To study measurement accuracy and cause of the errors. 3) Measurement sensitivity issues are resolved by new trapezoidal current mode (TZCM), where device is still operated at soft switching in HF and it brings practical benefits by adding delay between two phase-legs.

As shown in TABLE II, the presented results in this paper extends device characterisation area in terms of switching frequency, measurement time and device opearion conditions than our previous work presented in [15]. It is an overall achievement by using new measurement circuit and TZCM measurement method.

The paper is structured with following sections. In section II, new measurement circuit is proposed to characterise GaN device dynamic R_{DSon} value in both reverse and forward conduction. In section III, influence of measurement circuit L_c and other parameters (measurement probes deskew and oscilloscope offset voltage) on GaN device dynamic R_{DSon} measurement sensitivity is studied and trapezoidal current mode is proposed. In section IV, experimental measurement results are presented to validate proposed measurement circuit and method. The paper is concluded in section V.

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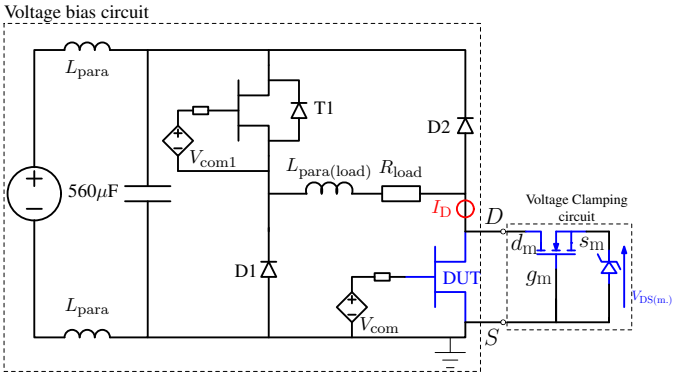
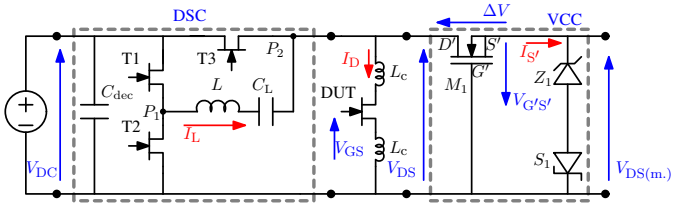
TABLE II: Comparison between our previous paper [15] and this paper

	Previous paper	This paper
Converter operation frequency	<10kHz, transient-state to 0.1s	until 1MHz, steady-state>100s
Purpose	Dynamic R_{DSon} characterisation & modelling	Accurate dynamic R_{DSon} characterisation
Paper structure	Characterisation circuit & modelling method	Characterisation circuit & characterisation method
Measurement time	$>1\mu$s	>10ns
Operation conditions	hard switching, forward conduction	hard & soft switching, forward & reverse conduction

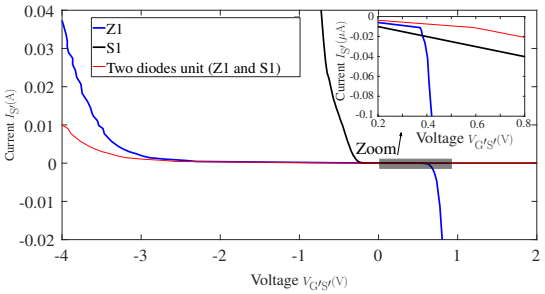


(a) Measurement circuit of our previous work in [15] to measure GaN device dynamic R_{DSon} only under forward conduction

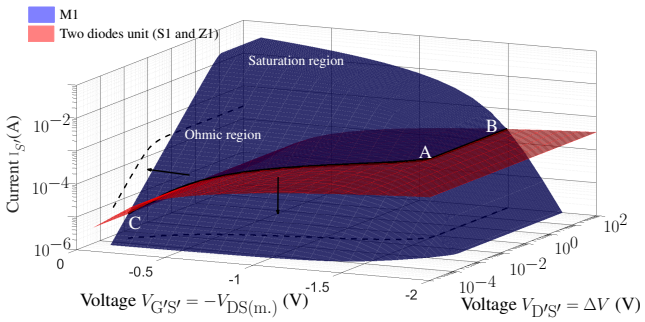


(b) Measurement circuit of this paper to measure GaN device dynamic R_{DSon} under reverse and forward conduction

Fig. 2: Comparison of the electrical circuit between our previous work and this work to measure GaN device dynamic R_{DSon}



(a) Two diodes unit characteristics



(b) M1 and two diodes unit characteristics

Fig. 3: VCC static characteristics

II. Measurement Circuit of GaN Device Dynamic R_{DSon} under Reverse and Forward Conduction

A. Measurement circuit

In our previously used electrical circuit shown in Fig. 2a [15], DUT can only operate in hard switching condition under forward conduction. In order to extend DUT operation conditions, another electrical circuit shown in Fig. 2b is proposed in this paper, where GaN device dynamic R_{DSon} value under both reverse and forward conduction can be characterised. In this circuit, the DSC part is a standard H-bridge circuit with two phases including decoupling capacitor C_{dec}, three identical power semiconductor devices T1, T2, T3. By connecting an output inductor L and capacitor C_{L} between nodes P_1 and P_2, DUT can operate at soft switching by alternating inductor current I_{L} direction. VCC part is constituted by three main components: a depletion-mode MOSFET M_1 with threshold voltage (V_{th}) inferior to zero, a Zener diode Z_1 and a Schottky diode S_1. The measured voltage $V_{\mathrm{DS(m.)}}$ is between cathode (K) of Z_1 and cathode of S_1, which also equals to the reverse gate voltage $V_{\mathrm{G'S'}}$ of M1 ($V_{\mathrm{G'S'}} = -V_{\mathrm{DS(m.)}}$). Following components are chosen in the VCC part: M1 (BSP135, 600V/100mA, $V_{\mathrm{th}} \approx$-1.6V), Z1 (BZT52C3V3, Zener voltage is 3.3V) and S1 (RB751SM-40FH, 40V/30mA). The choice of those components is justified by the circuit analysis below.

The relation of current and voltage of each diode Z1 and S1 together with their unit characteristics under their connection is shown in $V_{\mathrm{G'S'}}$-$I_{\mathrm{S'}}$ plot in Fig. 3a. It is to be noted that for the chosen components, M1 gate leakage current can be neglected in comparison with two diodes unit leakage current. Two diodes unit static characteristic is then represented in the form of a surface in Fig. 3b.

Static characteristics of M1 is also represented in Fig. 3b in the form of a surface, where M1 ohmic region and saturation region are illustrated. ΔV equals to $V_{\mathrm{D'S'}}$ voltage, which defines the measurement error when DUT is in ON-state.

It can be observed that there is an intersection line between two surfaces, which represents common static characteristics of M1 and two diodes unit. Depending on DUT operation conditions, static characteristics of VCC follows this intersection line.

- DUT OFF-state: Static characteristics of VCC is in intersection line AB. It is shown that $V_{\mathrm{G'S'}}$ voltage is around M1 V_{th}, so M1 is in OFF-state and it withstands almost the whole DC voltage ($\Delta V \approx V_{\mathrm{DC}}$). Measured $V_{\mathrm{DS(m.)}}$

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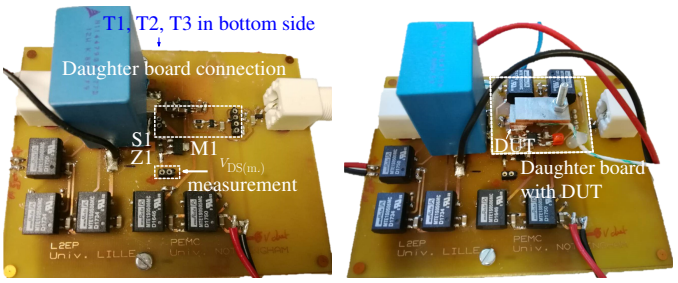


(a) Mother board (b) Mother board+Daughter board

Fig. 4: Measurement circuit realization

is around M1 opposite V_{th} value. In this condition, as shown in the projection of line AB in $I_{\text{S}'}$-$V_{\text{D}'\text{S}'}$ plane, leakage current of the chosen components in the VCC part is about 200μA, which will not cause components self-heating.

- DUT forward conduction: Static characteristics of VCC part is in intersection line AC. As long as DUT forward ON-state voltage $V_{\text{DSon(F.)}}$ is inferior to M1 opposite V_{th}, M1 operates in the ohmic region. As shown in the projection of line AC in $V_{\text{G}'\text{S}'}$-$V_{\text{D}'\text{S}'}$ plane, ΔV is much smaller than measured voltage $V_{\text{DS(m.)}}$ ($\Delta V = 10m$V when $V_{\text{DS(m.)}} = 1$V). Therefore, $V_{\text{DS(m.)}}$ equals to DUT forward ON-state voltage $V_{\text{DSon(F.)}}$.
- DUT reverse conduction: $V_{\text{G}'\text{S}'}$ voltage is positive in this condition, so M1 operates at ohmic region (ON-state resistance less than 50Ω). As reverse $I_{\text{S}'}$ is very small (less than 0.1μA, see Fig. 3a), ΔV is less than 5μV. Therefore, similar as DUT forward conduction, measured voltage $V_{\text{DS(m.)}}$ equals to DUT reverse ON-state voltage $V_{\text{DSon(R.)}}$.

Regarding the measurement accuracy, it can be noted that the proposed VCC is robust on drift of any temperature-dependent device static characteristics and it does not require any calibration of chosen devices, which is the case for using diode-type VCC in the literature [17]. Furthermore, it has reverse current blocking capability, which guarantees a wide operation range when DUT is under reverse conduction and during deadtime.

In terms of dynamic characteristics, proposed VCC improves the circuit dynamic response and M1 gate voltage overshoot, which is major drawback of transistor-type VCC analyzed by Gelagaev et al. in [19].

- DUT OFF-ON transition: As $V_{\text{G}'\text{S}'}$ is around M1 V_{th} value when DUT is in OFF-state, M1 gate source capacitance $C_{\text{G}'\text{S}'}$ only needs a little charge (less than 0.1nC) to increase $V_{\text{G}'\text{S}'}$ voltage superior to V_{th} during DUT ZVS transition. When $V_{\text{G}'\text{S}'}$ is superior to V_{th}, M1 output capacitance stored charge $Q_{\text{oss}'}$ (about 2nC when DUT switches at 200V) is dissipated in M1 channel quickly. Therefore, dynamic response of the VCC is fast to follow DUT OFF-ON transition. $Q_{\text{oss}'}$ of M1 is inferior to 20% of that of chosen DUT, which makes proposed VCC non-intrusive during measurement. Minimum $V_{\text{DS(m.)}}$ is determined by whether DUT body diode conducts during deadtime, which is normally a voltage drop of 2-3 V.
- DUT ON-OFF transition: Maximum $V_{\text{DS(m.)}}$ is determined by $V_{\text{G}'\text{S}'}$ overshoot voltage during transition, where it is clamped by the chosen Z1 (3.3V). As S1 has very small ON-state voltage drop, total overshoot voltage is inferior to 4V during DUT transition, which improves M1 gate voltage surge immunity.

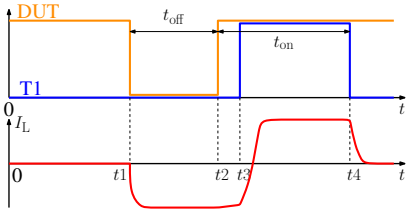
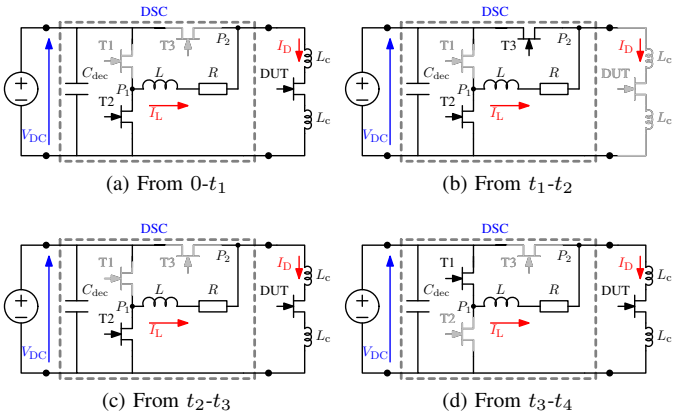


Fig. 5: Single-pulse control signal to measure power transistor reverse and forward ON-state resistance



(a) From 0-t_1 (b) From t_1-t_2

(c) From t_2-t_3 (d) From t_3-t_4

Fig. 6: Different circuit operation stages under given single-pulse control signal

It can be concluded that in all the above DUT operation conditions, measured $V_{\text{DS(m.)}}$ equals to the $V_{\text{G}'\text{S}'}$ variation, which is from a few negative volts (bigger than -3V) to a few positive volts (less than 4V). Therefore, a small voltage division (500mV/div or 1V/div) of the oscilloscope can be used in the measurement to have an improved resolution on V_{DSon} value compared with a direct measurement (with 50V/div or 100V/div).

Measurement circuit is realized with the photo shown in Fig. 4, where it is constituted by a mother board including same GaN-HEMT T1, T2, T3 (GS66502B, 650V/7.5A) with their gate drivers, alongside M1, Z1, S1 of VCC part and a daughter board including DUT with its gate driver. The advantage of this design is that only daughter board needs to be changed to characterise different types of DUT.

Validation of the circuit when device is operated at hard switching has been presented in [15]. Therefore, in this paper, measurement results are focused on device soft switching operation.

B. Measurement circuit validation

By replacing LC_{L} by a RL branch between P_1 and P_2 at first in Fig. 2b, a SiC-MOSFET (C2M0160120D, 1200V/19A,

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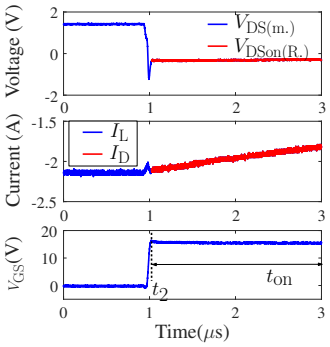
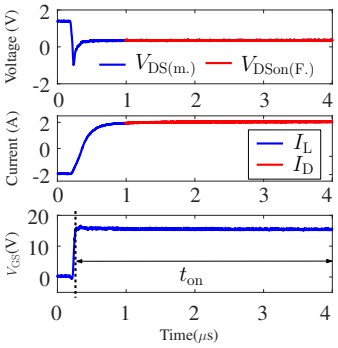
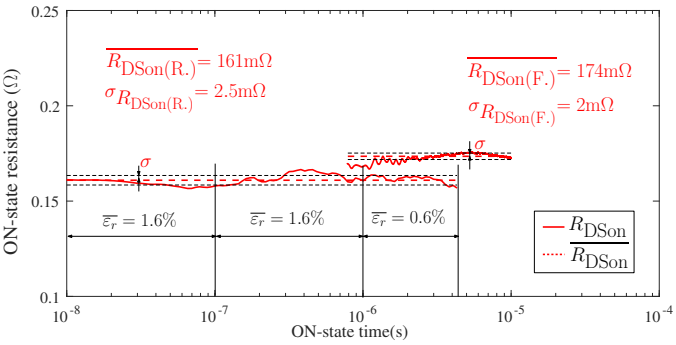


(a) Voltage and current waveform when SiC-MOSFET is reverse conduction



(b) Voltage and current waveform when SiC-MOSFET is forward conduction



(c) SiC-MOSFET Reverse and forward ON-state resistance

Fig. 7: SiC-MOSFET reverse and forward ON-state resistance measurement results

TABLE III: Comparison of SiC-MOSFET $\overline{R_{DSon(R.)}}$ and $\overline{R_{DSon(F.)}}$ between proposed method and device curve tracer

	$\overline{R_{DSon(R.)}}$	$\overline{R_{DSon(F.)}}$
Proposed method	161 mΩ	174mΩ
Device curve tracer	163 mΩ	169 mΩ
Relative measurement error	1.2%	2.9%

$V_{th} = 2.6$V) with static R_{DSon} around 200mΩ is characterised first by the above measurement circuit with single-pulse control signals of T1 and DUT given in Fig. 5. T2 and T3 are complimentary control signals of T1 and DUT respectively.

From 0-t_1 (see Fig. 6a), both DUT and T2 are in ON-state, therefore $I_L = 0$. Afterwards, both T3 and T2 are in ON-state from t_1-t_2 (see Fig. 6b), where I_L is charged in reverse conduction until steady state. DUT OFF-state time t_{off} is defined by this interval. Following that, both DUT and T2 are in ON-state from t_2-t_3 (see Fig. 6c), where DUT is turned on at ZVS at t_2 and it begins conducting reversely I_L (I_L decreases towards zero with time constant $\frac{L}{R}$). At final step t_3-t_4 (see Fig. 6d), both DUT and T1 are in ON-state, where I_L alternates direction until steady state in forward conduction (time constant is still determined by $\frac{L}{R}$). Thus, DUT ON-state time t_{on} is defined by t_2-t_4 interval. A detailed analysis on DUT ZVS process has been presented by authors in [20]. Under this control sequence, DUT R_{DSon} under reverse and forward conduction ($R_{DSon(R.)}$ and $R_{DSon(F.)}$) can be obtained at t_2-t_3 interval and t_3-t_4 interval respectively under constant I_L. $R_{DSon(R.)}$ can be obtained under long t_{on} by choosing a big L and $R_{DSon(F.)}$ can be obtained quickly after I_L transition by using a small L. Therefore, by setting t_2-t_3 stage length accordingly, both $R_{DSon(R.)}$ and $R_{DSon(F.)}$ can be obtained under similar t_{on} scale to compare.

As SiC-MOSFET does not suffer any dynamic resistance variation as GaN transistor, its obtained reverse and forward ON-state resistance by the proposed circuit can be used as a reference to verify proposed circuit dynamic response and accuracy. Measurement condition is: $V_{DC} = 200$V and stabilized DUT ON-state current is 2A. I_L is obtained in experiment measurement, and $I_L = I_D$ when DUT V_{GS} reaches ON-state gate voltage.

For the characterised SiC-MOSFET, as shown in Fig. 7a when DUT is in OFF-state, obtained $V_{DS(m.)}$ is clamped to reverse V_{th} of chosen depletion MOSFET ($V_{th} \approx -1.6$V), which confirms the above circuit analysis and when it is under reverse conduction, DUT reverse ON-state voltage $V_{DSon(R.)}$ and current I_D can be measured quickly after $V_{GS} = 16$V, which confirms the fast response of the presented measurement circuit. As shown in Fig. 7b when it is under forward conduction, DUT forward ON-state voltage $V_{DSon(F.)}$ and current I_D are measured when I_L is stabilized.

DUT $R_{DSon(R.)}$ and $R_{DSon(F.)}$ are then compared in Fig. 7c to show its variation with ON-state time t_{on}. Obtained DUT average reverse ON-state resistance ($\overline{R_{DSon(R.)}}$) by the proposed measurement method is about 161mΩ, even with some noise on the measurement data, $R_{DSon(R.)}$ standard derivation ($\sigma_{R_{DSon(R.)}}$) is about 2.5mΩ, which is only 1.6% to $\overline{R_{DSon(R.)}}$. In terms of DUT average forward ON-state resistance ($\overline{R_{DSon(F.)}}$), obtained value is about 174mΩ with 2mΩ on $\sigma_{R_{DSon(F.)}}$ (1.1% to $\overline{R_{DSon(F.)}}$). Those small relative $\sigma_{R_{DSon(R.)}}$ and $\sigma_{R_{DSon(F.)}}$ values prove the measurement consistency of the proposed circuit.

$\overline{R_{DSon(R.)}}$ and $\overline{R_{DSon(F.)}}$ between proposed method is then compared in TABLE III with their values obtained in device curve tracer (B1505A). Relative measurement error between the proposed method to the curve tracer is inferior to 2.9%, which confirms the measurement accuracy of the proposed circuit. It is to be noted that for SiC-MOSFET, obtained device $\overline{R_{DSon(R.)}}$ is slightly smaller than $\overline{R_{DSon(F.)}}$. This difference is supposed to be the SiC-MOSFET body diode conduction when DUT is under reverse conduction, which lowers DUT reverse $R_{DSon(R.)}$.

Response time of VCC is an important parameter to judge if it can be used to measure DUT dynamic R_{DSon} when DUT is applied in high frequency converter, no matter it is under soft or hard switching. To verify fast response of proposed VCC, the term of relative measurement error ($\varepsilon_r = \frac{|R_{DSon(R.)}(t) - \overline{R_{DSon(R.)}}|}{\overline{R_{DSon(R.)}}}$) is used. Its average value ($\overline{\varepsilon_r}$) of different time intervals ($10ns$~$100ns$, $100ns$~$1\mu s$ and after $1\mu s$) are then compared in Fig. 7c. $\overline{\varepsilon_r}$ is inferior to 1.6% when t_{on} is longer than $10ns$, which confirms fast dynamic response of proposed VCC to obtain DUT R_{DSon} when DUT switches in megahertz range power converter.

The proposed circuit is validated in this section and a control

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signal of trapezoidal current mode will be presented in the next section to improve measurement sensitivity when device switches in high frequency converter.

III. Measuring GaN device dynamic R_{DSon} in high frequency converter

The conventional device characterisation method based on triangle current mode (TCM) is used to measure GaN device dynamic R_{DSon} when device operates in high frequency converter [17], [21]. Measurement error caused by unavoidable circuit parasitic inductance L_{c} under TCM on device ON-state resistance has been raised by authors in [21]. However, there is no solution proposed to compensate the measurement error. In this section, different sensitivity issues caused by unavoidable L_{c} and measurement probes deskew are studied. In order to improve measurement sensitivity when device is operated in high frequency power converter, a trapezoidal current mode (TZCM) is proposed accordingly.

A. Triangle current mode

Under I_{D} current fast transition of TCM, the influence of unavoidable L_{c} (see Fig. 2b) due to PCB tracks, device packaging etc., deskew (t_{dk}) between voltage probe and current probe, and oscilloscope offset voltage accuracy (V_{off}, due to internal offset voltage source precision [22]) on dynamic R_{DSon} measurement sensitivity needs to be carefully studied when DUT is operated in high frequency converter.

Real DUT R_{DSon} is defined by:

$$R_{\mathrm{DSon}}(t) = \frac{V_{\mathrm{DSon}}(t)}{I_{\mathrm{D}}(t)} \tag{1}$$

By considering the presence of L_{c} and oscilloscope offset V_{off}, measured apparent voltage $V_{\mathrm{DSon(m.)}}$ is:

$$V_{\mathrm{DSon(m.)}}(t) = I_{\mathrm{D}}(t) \cdot R_{\mathrm{DSon}}(t) + L_{\mathrm{c}} \frac{\mathrm{d}I_{\mathrm{D}}(t)}{\mathrm{d}t} + V_{\mathrm{off}} \tag{2}$$

By considering t_{dk} between current probe and voltage probe, relation between measured apparent current $I_{\mathrm{D(m.)}}(t)$ and real current $I_{\mathrm{D}}(t)$ can then be further expressed by:

$$I_{\mathrm{D(m.)}}(t) = I_{\mathrm{D}}(t) - t_{\mathrm{dk}} \cdot \frac{\mathrm{d}I_{\mathrm{D}}(t)}{\mathrm{d}t} \tag{3}$$

By combining eq.(2) and eq.(3) together, relative measurement error is therefore obtained by:

$$\begin{aligned} \varepsilon_r = \frac{R_{\mathrm{DSon(m.)}}(t) - R_{\mathrm{DSon}}(t)}{R_{\mathrm{DSon}}(t)} = f\left(L_{\mathrm{c}}, t_{\mathrm{dk}}, V_{\mathrm{off}}\right) = \\ \frac{t_{\mathrm{dk}}}{I_{\mathrm{D(m.)}}(t)} \cdot \frac{\mathrm{d}I_{\mathrm{D}}(t)}{\mathrm{d}t} + \frac{L_{\mathrm{c}}}{R_{\mathrm{DSon}}(t) \cdot I_{\mathrm{D(m.)}}(t)} \cdot \frac{\mathrm{d}I_{\mathrm{D}}(t)}{\mathrm{d}t} \\ + \frac{V_{\mathrm{off}}}{R_{\mathrm{DSon}}(t) \cdot I_{\mathrm{D(m.)}}(t)} \end{aligned} \tag{4}$$

Supposing a symmetrical TCM is applied with D=50% and $I_{\mathrm{D(m.)}}(t)$ is measured at its maximal value, following term $\frac{1}{I_{\mathrm{D(m.)}}(t)} \cdot \frac{\mathrm{d}I_{\mathrm{D}}(t)}{\mathrm{d}t}$ can be simplified into $4f_{\mathrm{sw}}$, which is only dependent on DUT switching frequency f_{sw}. The influence of each variable L_{c}, t_{dk} and V_{off} on ε_r is obtained by partial derivative of the function $f\left(L_{\mathrm{c}}, t_{\mathrm{dk}}, V_{\mathrm{off}}\right)$. They are then compared by following equations:

$$\begin{aligned} g_{t_{\mathrm{dk}}} &= \frac{\partial f\left(t_{\mathrm{dk}}, L_{\mathrm{c}}, V_{\mathrm{off}}\right)}{\partial t_{\mathrm{dk}}} = 4f_{\mathrm{sw}} \\ g_{L_{\mathrm{c}}} &= \frac{\partial f\left(t_{\mathrm{dk}}, L_{\mathrm{c}}, V_{\mathrm{off}}\right)}{\partial L_{\mathrm{c}}} = \frac{4f_{\mathrm{sw}}}{R_{\mathrm{DSon}}(t)} \\ g_{V_{\mathrm{off}}} &= \frac{\partial f\left(t_{\mathrm{dk}}, L_{\mathrm{c}}, V_{\mathrm{off}}\right)}{\partial V_{\mathrm{off}}} = \frac{1}{R_{\mathrm{DSon}}(t) \cdot I_{\mathrm{D(m.)}}(t)} \end{aligned} \tag{5}$$

Supposing DUT switches at 1MHz, measured $I_{\mathrm{D(m.)}}(t)$ is about 2A and $R_{\mathrm{DSon}}(t)$ is about 0.2Ω (same condition as results presented in section II-B). The influence of each term on measurement error is obtained below.

- $g_{t_{\mathrm{dk}}}$: the influence of t_{dk} on measurement error shows directly proportional dependency on DUT switching frequency. When $f_{\mathrm{sw}} = 1\mathrm{MHz}$, $g_{t_{\mathrm{dk}}} = 0.004/n\mathrm{s}$, which means $1n$s of uncorrected deskew between voltage and current probes results in 0.4% measurement error. Even though different probes deskew detecting methods have been analyzed in [23], it still needs special caution to accurately obtain this value.
- $g_{L_{\mathrm{c}}}$: the influence of L_{c} on measurement error shows directly proportional dependency on DUT switching frequency and inversely proportional dependency on DUT R_{DSon} value. For the characterised DUT as an example, $g_{L_{\mathrm{c}}} = 0.02/n\mathrm{H}$, which means $1n$H of unknown L_{c} value results in 2% measurement error. It is to be noted that part of L_{c} is from DUT packaging, which is not always an obvious parameter for power electronics engineers.
- $g_{V_{\mathrm{off}}}$: the influence of V_{off} on measurement error shows inversely proportional dependency on DUT R_{DSon} value and switching current. In the chosen example, $g_{V_{\mathrm{off}}} = 0.0025/m\mathrm{V}$, which means $1m$V of oscilloscope offset voltage error results in 0.25% measurement error. It is to be noted that unlike $g_{t_{\mathrm{dk}}}$ and $g_{L_{\mathrm{c}}}$, $g_{V_{\mathrm{off}}}$ is not dependent on f_{sw} and it is only determined by oscilloscope vertical voltage range setting, of which the value can be easily calibrated.

In the experimental work of this paper, measurement oscilloscope is 8-bit with 1GHz bandwidth (DPO4104B). A Hall effect current probe (100MHz, 1A/V) is used to measure I_{L} and a passive voltage probe (500MHz) is used to measure $V_{\mathrm{DS(m.)}}$. t_{dk} of chosen probes is around $10n$s, L_{c} is estimated to be $10n$H and V_{off} is within 1.5% of full voltage range (5V with 500mV/div). Therefore, each measurement error is: $g_{t_{\mathrm{dk}}} = 4\%$, $g_{L_{\mathrm{c}}} = 20\%$ and $g_{V_{\mathrm{off}}} = 19\%$. It is to be noted that DUT can be placed at the same board with DSC and VCC to reduce L_{c}. However, it is not convenient in this design to characterise different devices.

Thus, total measurement error by applying the error propagation is:

$$g_{total} = \sqrt{g_{t_{\mathrm{dk}}}^2 + g_{L_{\mathrm{c}}}^2 + g_{V_{\mathrm{off}}}^2} \approx 28\% \tag{6}$$

It is shown from the above analysis that special caution is necessary to measure DUT R_{DSon} under TCM, which requires

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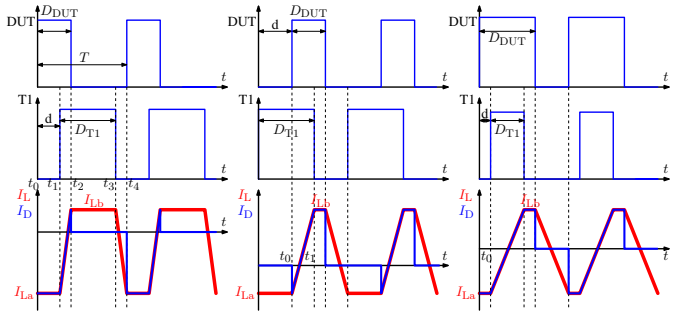
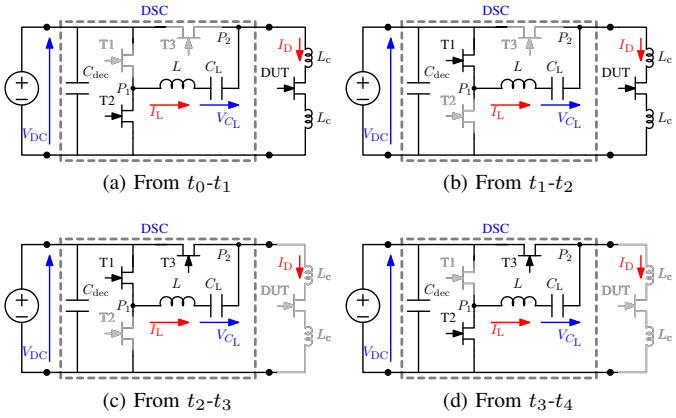


(a) Sub-mode 1 (b) Sub-mode 2 (c) Sub-mode 3

Fig. 8: Three current sub-modes of trapezoidal current mode



(a) From t_0-t_1 (b) From t_1-t_2

(c) From t_2-t_3 (d) From t_3-t_4

Fig. 9: Different circuit operation stages under sub-mode1 of TZCM

additional knowledge to accurately obtain t_{dk} and L_{c} and exclude their influence on obtained R_{DSon}. In order to improve measurement accuracy, it is proposed in the next subsection to measure DUT R_{DSon} under TZCM.

B. Trapezoidal current mode

Unlike TCM, where DUT and T1 share the same control signal, control signal of T1 is different from DUT in TZCM. As DSC is a standard H-bridge, a phase shift d is applied between two legs. Ignoring effect of parasitic inductance L_{c}, when circuit is operated under TZCM, it should be ensured that there is no voltage across L when both legs are in the same switching state ("DUT ON, T1 OFF" and "DUT OFF, T1 ON"). Since these states correspond to nodes P_1 and P_2 having the same potential, this implies that there is no net voltage across capacitor C_{L} ($V_{C_{\mathrm{L}}} = 0$). Consequently, both legs must be controlled with the same duty cycle: $D_{\mathrm{T1}} = D_{\mathrm{T3}}$, which means $D_{\mathrm{T1}} + D_{\mathrm{DUT}} = 1$. When the two legs are in different switching states, V_{DC} is applied across L with phase shift controlling the amplitude of I_{L} trapezoidal waveform. Depending on DUT duty cycle (D_{DUT}), there are three current sub modes in TZCM method, which is illustrated in Fig. 8. T2 and T3 are still complementary control signals of T1 and DUT respectively with a deadtime τ. As τ is much smaller than switching period, it is neglected in the analysis.

1) Sub-mode 1: From t_0-t_1 (see Fig. 9a): DUT is turned on by negative load current I_{La} at t_0 in ZVS. As T1 is delayed to DUT control signal by d, DUT is in reverse conduction by an almost constant I_{La} during the delay time. Therefore, DUT $R_{\mathrm{DSon(R.)}}$ can be measured under I_{La}. From t_1-t_2 (see Fig. 9b): both DUT and T1 are in ON-state, therefore I_{L} is charged by V_{DC} at this stage. From t_2-t_3 (see Fig. 9c): both T1 and T3 are in ON-state, I_{L} is with almost constant value I_{Lb}. From t_3-t_4 (see Fig. 9d): both T2 and T3 are in ON-state, I_{L} is thus reversely charged by V_{DC}. Therefore, following two equations are applied:

$$\begin{aligned} V_{\mathrm{DC}} &= L \cdot \frac{(I_{\mathrm{Lb}} - I_{\mathrm{La}}) \cdot f_{\mathrm{sw}}}{D_{\mathrm{DUT}} - d} \\ I_{\mathrm{La}} \cdot d + I_{\mathrm{Lb}} &\cdot (D_{\mathrm{T1}} - (D_{\mathrm{DUT}} - d)) \\ &+ (I_{\mathrm{La}} + I_{\mathrm{Lb}}) \cdot (D_{\mathrm{DUT}} - d) = 0 \end{aligned} \tag{7}$$

By simplifying eq.(7), I_{La} can be expressed by:

$$I_{\mathrm{La}} = -\frac{V_{\mathrm{DC}} \cdot (D_{\mathrm{DUT}} - d)}{f_{\mathrm{sw}} \cdot L} \cdot D_{\mathrm{T1}} \tag{8}$$

2) Sub-mode 2: Control signal of DUT is delayed to T1 by d, so DUT is turned on by negative load current I_{La} at t_0 in ZVS. As both T1 and DUT remain ON-state afterwards, I_{L} is charged by V_{DC} to alternate direction. When T1 is turned off at t_1, DUT is in forward conduction by an almost constant I_{Lb} until it is turned off. Therefore, DUT $R_{\mathrm{DSon(F.)}}$ can be measured under I_{Lb}. Following two equations are applied:

$$\begin{aligned} V_{\mathrm{DC}} &= L \cdot \frac{(I_{\mathrm{Lb}} - I_{\mathrm{La}}) \cdot f_{\mathrm{sw}}}{D_{\mathrm{T1}} - d} \\ I_{\mathrm{La}} \cdot d + I_{\mathrm{Lb}} &\cdot (D_{\mathrm{DUT}} - (D_{\mathrm{T1}} - d)) \\ &+ (I_{\mathrm{La}} + I_{\mathrm{Lb}}) \cdot (D_{\mathrm{T1}} - d) = 0 \end{aligned} \tag{9}$$

I_{Lb} can then be expressed by:

$$I_{\mathrm{Lb}} = \frac{V_{\mathrm{DC}} \cdot (D_{\mathrm{T1}} - d)}{f_{\mathrm{sw}} \cdot L} \cdot D_{\mathrm{T1}} \tag{10}$$

3) Sub-mode 3: DUT is turned on by negative load current I_{La} at t_0 in ZVS. Similar as sub-mode 1, DUT $R_{\mathrm{DSon(R.)}}$ can be measured under an almost constant I_{La} until T1 is turned on. I_{L} is charged by V_{DC} to alternate direction during T1 ON-state. Afterwards, similar as sub-mode 2, DUT $R_{\mathrm{DSon(F.)}}$ can be measured under an almost constant I_{Lb}. Following two equations are applied:

$$\begin{aligned} V_{\mathrm{DC}} &= L \cdot \frac{(I_{\mathrm{Lb}} - I_{\mathrm{La}}) \cdot f_{\mathrm{sw}}}{D_{\mathrm{T1}}} \\ I_{\mathrm{La}} \cdot d + I_{\mathrm{Lb}} &\cdot (D_{\mathrm{DUT}} - (D_{\mathrm{T1}} + d)) \\ &+ (I_{\mathrm{La}} + I_{\mathrm{Lb}}) \cdot D_{\mathrm{T1}} = 0 \end{aligned} \tag{11}$$

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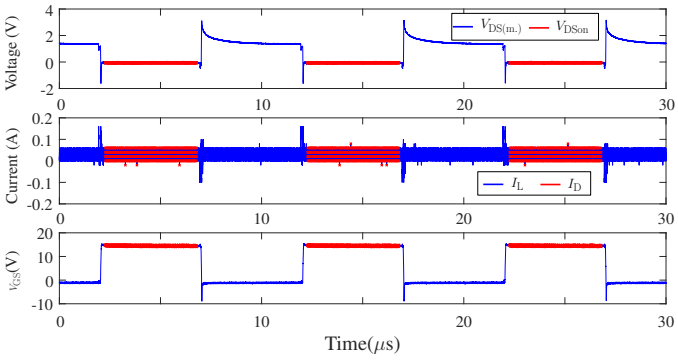


Fig. 10: Obtained device $V_{\mathrm{DS(m.)}}$, I_{D} and V_{GS} waveform to calibrate oscilloscope V_{off}

I_{La} and I_{Lb} can then be expressed by:

$$I_{\mathrm{La}} = -\frac{V_{\mathrm{DC}} \cdot (D_{\mathrm{DUT}} - d)}{f_{\mathrm{sw}} \cdot L} \cdot D_{\mathrm{T1}}$$
$$I_{\mathrm{Lb}} = \frac{V_{\mathrm{DC}} \cdot (D_{\mathrm{T1}} + d)}{f_{\mathrm{sw}} \cdot L} \cdot D_{\mathrm{T1}} \quad (12)$$

By adding one degree of liberty d in TZCM, $R_{\mathrm{DSon(R.)}}$ and $R_{\mathrm{DSon(F.)}}$ can be measured under same I_{La} and I_{Lb} value with a constant L value in different f_{sw} and D_{DUT}, which is not the case by TCM method, where L value needs to be changed with f_{sw} and D_{DUT} to keep load current constant.

It is to be noted that for safety reason, it is preferred to add an external capacitor C_{L} in the circuit to withstand any unbalanced average voltage between P_1 and P_2 to be applied to L, which may result in infinite increase of I_{L}. Unbalanced average voltage may be caused by inhomogeneous delays in the gate driver of each transistor (it may slightly influence on D_{DUT} and D_{T1}), ON-state voltage drops of the transistors and deadtime of two transistors of each bridge (it may slightly influence on each stage length). The resulting $V_{C_{\mathrm{L}}}$ value can be neglected in all the experimental results, so I_{L} is still under trapezoidal waveform, which can be proved by measurement results presented in section IV of the paper.

It can be also concluded that unlike TCM method, DUT R_{DSon} is measured at constant load current, which simultaneously resolves two of the measurement sensitivity issues highlighted in section III-A regarding the influence of measurement probe t_{dk} and of parasitic circuit and package inductance L_{c} on measurement results. Only V_{off} needs to be predetermined for accurate measurement, which will be presented in the next subsection.

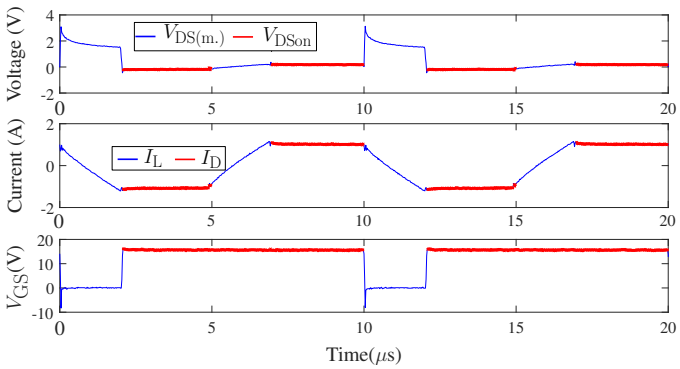
C. V_{off} calibration

In order to calibrate oscilloscope offset voltage V_{off}, L and C_{L} are disconnected from the measurement circuit in Fig. 2b. When DUT (SiC-MOSFET) switches at 100kHz and $V_{\mathrm{DC}} = 200$V, obtained device $V_{\mathrm{DS(m.)}}$, I_{D} and V_{GS} is shown in Fig. 10.

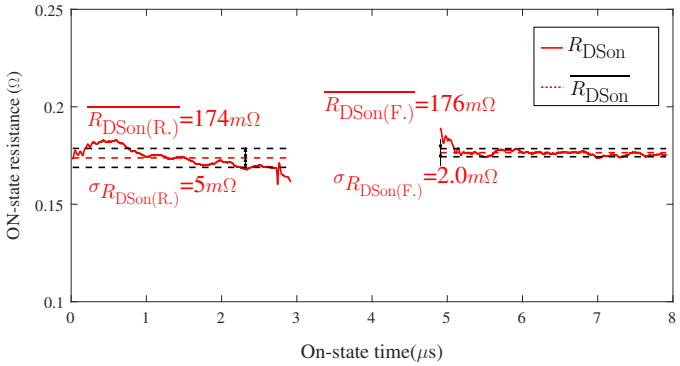
When V_{GS} equals to 16V, DUT is in ON-state. As there is no current flowing through DUT, both of measured I_{D} and V_{DSon} should be zero. The above measurement process is repeated 20 times by connecting and disconnecting voltage and current probes. Therefore, V_{off} mean value (μ) and standard derivation (σ) on both voltage ($V_{\mathrm{off}}(V)$) and current ($V_{\mathrm{off}}(I)$) measurement are obtained and they are compared with each oscilloscope channel full range value (V_{FS}) in TABLE IV.

TABLE IV: V_{off} calibrated results on both voltage and current measurement

	μ (mV)	σ (mV)	V_{FS} (V)	$\frac{\mu}{V_{\mathrm{FS}}}$
$V_{\mathrm{off}}(V)$	-59	3	5 (0.5V/div.)	1.2%
$V_{\mathrm{off}}(I)$	27	0.6	5 (0.5V/div.)	0.5%



(a) Measured waveforms



(b) $R_{\mathrm{DSon(R.)}}$ and $R_{\mathrm{DSon(F.)}}$ of one switching period

Fig. 11: SiC-MOSFET reverse and forward ON-state resistance measurement results when device switches at 100kHz by proposed TZCM

It can be concluded that obtained V_{off} is consistent by a small σ value. Meanwhile, obtained $\frac{\mu}{V_{\mathrm{FS}}}$ shows relative voltage offset error to channel full range voltage, which might be different in different manufacturers. After compensation, σ remains an unpredictable error source. However, its influence on measurement results is less than 1% ($g_{V_{\mathrm{off}}} \times \sigma = 0.75\%$).

After calibrating V_{off}, R_{DSon} of both SiC-MOSFET and GaN-HEMT are obtained when they operate continuously in power converter.

IV. Measurement Results

A. SiC-MOSFET

In order to validate the proposed TZCM method, R_{DSon} of the same SiC-MOSFET is measured when device is switching

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at 100kHz ($D_{\mathrm{DUT}} = 80\%$), $V_{\mathrm{DC}} = 200$V to compare with its values obtained in Fig. 7c. Obtained device $V_{\mathrm{DS(m.)}}$, I_{L} and V_{GS} waveform are shown in Fig. 11a under sub-mode 3 of TZCM. When $V_{\mathrm{GS}} = 16$V, V_{DSon} and I_{D} can be obtained from measured $V_{\mathrm{DS(m.)}}$ and I_{L} waveforms. Therefore, both $R_{\mathrm{DSon(R.)}}$ and $R_{\mathrm{DSon(F.)}}$ can be measured simultaneously at one switching period under constant current.

As compared in Fig. 11b, obtained $\overline{R_{\mathrm{DSon(R.)}}}$ is about 174mΩ, and its $\sigma_{R_{\mathrm{DSon(R.)}}}$ is about 5mΩ, which is 2.9% to $\overline{R_{\mathrm{DSon(R.)}}}$ value. Obtained $\overline{R_{\mathrm{DSon(F.)}}}$ is about 176mΩ, and its $\sigma_{R_{\mathrm{DSon(F.)}}}$ is about 2.0mΩ, which is 1.1% to $\overline{R_{\mathrm{DSon(F.)}}}$ value. Both $\overline{R_{\mathrm{DSon(R.)}}}$ and $\overline{R_{\mathrm{DSon(F.)}}}$ are slightly increased (7.4% and 1.7%) in comparison with their values shown in TABLE. III, which may be due to DUT junction temperature T_{j} difference when it is operated at 100kHz. Measurement consistency and accuracy of the proposed measurement circuit and TZCM method can be verified by those results.

B. GaN-HEMT

1) Single-pulse mode: In order to investigate GaN transistor $R_{\mathrm{DSon(R.)}}$ and $R_{\mathrm{DSon(F.)}}$ with t_{on}, its dynamic R_{DSon} under both reverse and forward conduction is measured at first under single-pulse mode by the same method presented in section II-B.

A GaN-HEMT (GS66502B, 650V/7.5A, $V_{\mathrm{th}} = 1.3$V) with similar static R_{DSon} of around 200mΩ is characterised when t_{off} of Fig. 5 is set to be $10m$s and 10s. As shown in Fig. 12a, in comparison with device static R_{DSon} value (0.195Ω), device dynamic R_{DSon} value can increase to 50% bigger and it increases more with longer t_{off}. It is also observed in the measurement results that obtained $R_{\mathrm{DSon(F.)}}$ corresponds well to the $R_{\mathrm{DSon(R.)}}$ value on the common t_{on} range ($800n$s to 3μs), which confirms that dynamic R_{DSon} value decreases to static R_{DSon} value with t_{on}. This result conforms to reported GaN device dynamic R_{DSon} variation in the literature [17] and can be used as a reference to verify measurement results when device is operated in high frequency switching converter. It is also shown in the results that GaN-HEMT does not have body-diode to lower its $R_{\mathrm{DSon(R.)}}$ than $R_{\mathrm{DSon(F.)}}$. Obtained device dynamic R_{DSon} under both reverse and forward conduction is due to trapped charge.

Another GaN gate injection transistor (GIT, PGA26E19BA, 600V/13A) has been tested with the same method under conditions: $V_{\mathrm{DS}} = 200$V, $I_{\mathrm{D}} = 2$A and $t_{\mathrm{off}} = 10$s. As presented in Fig. 12b, it reveals again that obtained $R_{\mathrm{DSon(R.)}}$ corresponds to $R_{\mathrm{DSon(F.)}}$ value on the common t_{on} range, owing to the accuracy of proposed measurement circuit. For this GIT, dynamic R_{DSon} increases twice bigger than its static R_{DSon} value when t_{on} is less than $100n$s, revealing an non-negligible effect on device conduction losses.

2) Continuous mode: When device is switching at 1MHz ($D_{\mathrm{DUT}} = 50\%$) and $V_{\mathrm{DC}} = 200$V, dynamic R_{DSon} of the same GaN-HEMT is then measured by the proposed TZCM and conventional TCM method, where the measurement results are shown in Fig. 13. It can be noted that when DUT is fully turned ON at $V_{\mathrm{GS}} = 6$V, obtained V_{DSon} is negative in all the experimental results, which confirms that DUT is under

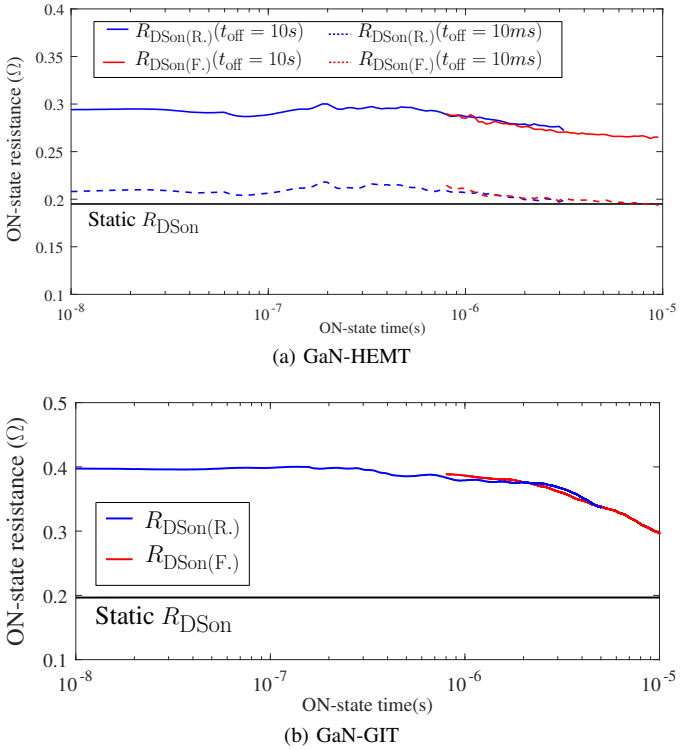

Fig. 12: Reverse and forward dynamic R_{DSon} of different GaN transistors

reverse conduction and it realizes ZVS soft switching at turn-ON transition, as its C_{oss} is fully discharged by I_{L} during deadtime.

By using TZCM method, $R_{\mathrm{DSon(R.)}}$ is obtained under constant reverse I_{D} at sub-mode 1 (see Fig. 13a) and $R_{\mathrm{DSon(F.)}}$ is obtained under constant forward I_{D} at sub-mode 2 (see Fig. 13b). By using conventional TCM method, device R_{DSon} is obtained when I_{D} is around 1A in both reverse and forward conduction (see Fig. 13c). Obtained R_{DSon} and their mean value $\overline{R_{\mathrm{DSon}}}$ over the chosen conduction time by the two methods are then compared in Fig. 14. $\sigma_{R_{\mathrm{DSon}}}$ is inferior to $3m\Omega$ in all the obtained data, which confirms again the measurement consistency by using the proposed circuit. Therefore, $\overline{R_{\mathrm{DSon}}}$ can be used to compare the measurement accuracy of different methods.

By conventional TCM method, obtained GaN-HEMT dynamic $\overline{R_{\mathrm{DSon(R.)}}}$ is 308mΩ and $\overline{R_{\mathrm{DSon(F.)}}}$ is 365mΩ. The difference ($\Delta R = \overline{R_{\mathrm{DSon(R.)}}} - \overline{R_{\mathrm{DSon(F.)}}}$) is -56mΩ, which is about -18.5% to $\overline{R_{\mathrm{DSon(R.)}}}$ value. The increase of device dynamic ON-state resistance value during one switching period with ON-state time does not agree with GaN device physics shown in Fig. 12a. As shown in section III-A, influence of t_{dk} and L_{c} on measurement sensitivity becomes critical under fast I_{L} transition (more than 5A/μs as shown in Fig. 13c). This negative ON-state resistance difference can be further explained by eq.(2), where the term $\frac{\mathrm{d}I_{\mathrm{D}}}{\mathrm{d}t}$ lowers apparent $V_{\mathrm{DSon(m.)}}$ value when DUT is in reverse conduction and increases $V_{\mathrm{DSon(m.)}}$ value when DUT is in forward conduction.

In comparison, by proposed TZCM, obtained GaN-HEMT $\overline{R_{\mathrm{DSon(R.)}}}$ is 331mΩ and $\overline{R_{\mathrm{DSon(F.)}}}$ is 327mΩ at one period.

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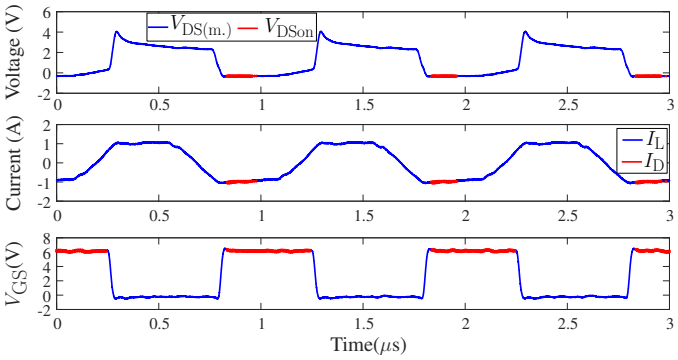
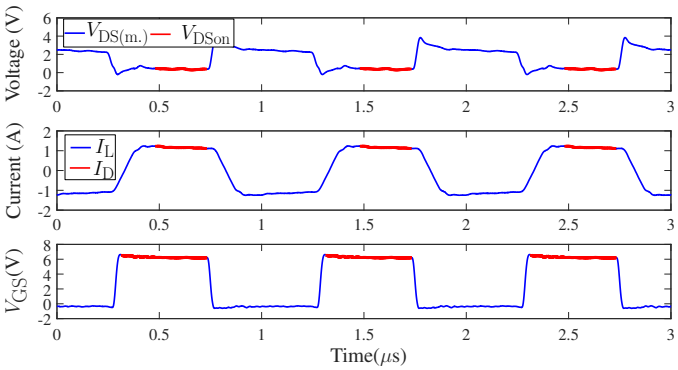
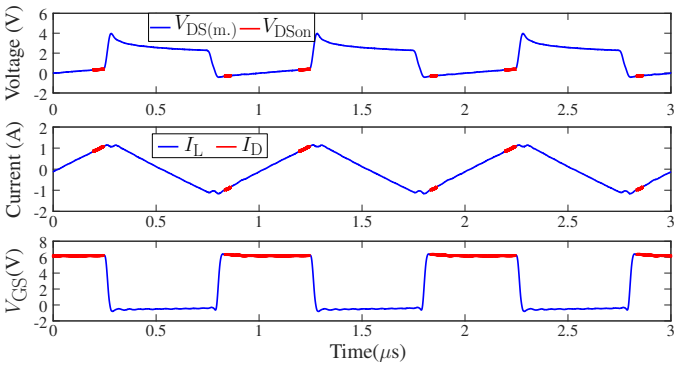


(a) Device switches at sub-mode 1 of TZCM



(b) Device switches at sub-mode 2 of TZCM



(c) Device switches at TCM

Fig. 13: GaN-HEMT dynamic ON-state resistance measurement results by proposed TZCM and by conventional TCM when device switches at 1MHz

ΔR is only 4mΩ, which is about 1.2% to $\overline{R_{\mathrm{DSon(R.)}}}$ value. This slight decrease of device dynamic R_{DSon} with ON-state time at one switching period conforms to obtained GaN device dynamic ON-state resistance values in Fig. 12a, which also demonstrates the advantage of proposed TZCM method over conventional TCM method on measurement accuracy when circuit L_{c} cannot be ignored in high frequency power converter. It is to be noted that L_{c} can be reduced by using an all-integration PCB board. Nevertheless, as presented in eq.(5), designers would still have unavoidable $g_{L_{\mathrm{c}}}$ measurement issue depending on device switching frequency and R_{DSon} value by using conventional TCM method.

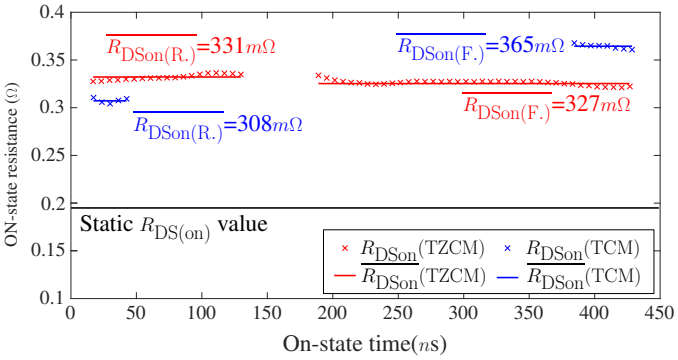


Fig. 14: GaN-HEMT dynamic ON-state resistance comparison between TZCM and TCM

V. Conclusion

In this paper, a measurement circuit is proposed to measure GaN transistor dynamic ON-state resistance R_{DSon} when device is operated in high frequency converters. The measurement circuit is constituted by a standard H-bridge to control device switching (DSC) and a voltage clamping circuit (VCC) to reduce measured voltage from full DC bus voltage to a few volts, so as to improve measurement resolution. In comparison with different state-of-the-art of VCC, the proposed one has a simple structure (only three components), good dynamic response (10 ns) and can be used to measure power transistor both reverse and forward R_{DSon} with robust accuracy, which is suitable for device application in soft switching circuit. The measurement circuit is then validated by measuring on SiC-MOSFET with constant R_{DSon} value when device is under both reverse and forward conduction.

Afterwards, influence of unavoidable common parasitic inductance L_{c} between DSC and VCC, voltage and current probes deskew (t_{dk}) and oscilloscope offset voltage (V_{off}) on measurement sensitivity is analyzed, which shows potential sensitivity issue in conventional device R_{DSon} measurement by triangle current mode (TCM) method when device operates in high frequency converter. In order to eliminate the influence of L_{c} and t_{dk} on measurement sensitivity, a trapezoidal current mode (TZCM) method is proposed. By adding a phase shift between two phases of a H-bridge, transistor R_{DSon} can be obtained under an almost constant drain current. Therefore, only V_{off} needs to be calibrated in TZCM method, in which its value can be easily obtained by a measurement when DUT operates without current.

Reverse and forward ON-state resistances ($R_{\mathrm{DSon(R.)}}$ and $R_{\mathrm{DSon(F.)}}$) of the same SiC-MOSFET are measured by TZCM when device operates at 100kHz. Measurement results conform to their values obtained by a curve tracer, which validates consistency and accuracy of proposed TZCM method. Following that, when device switches at 1MHz, GaN device dynamic R_{DSon} is measured by both TZCM method and conventional TCM method. It is shown in the measurement results the sensitivity issue caused by t_{dk} and L_{c} in conventional TCM method under fast transition of drain current, which causes a non-physical device dynamic R_{DSon} increase with ON-state time. The advantage of proposed TZCM method on

measurement accuracy is thus justified.

Based on the results of the paper, a GaN device model taking into consideration of device dynamic R_{DSon} evaluation under different operation conditions can be built and validated, which will be the subject of future communications.

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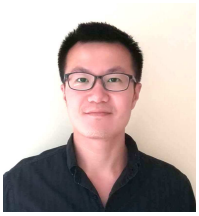

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